

HD29050

Dual Differential Line Drivers/Receivers With 3 State Outputs

REJ03D0304-0300Z
 (Previous ADE-205-034A (Z))
 Rev.3.00
 Jul.16.2004

Description

The HD29050 features differential line drivers/receivers with three state output designed to meet the spec of EIA RS-422A and 423A. Each device has two drivers/receivers in a 16 pin package.

The device becomes in enable state when active high for a driver and active low for a receiver.

Features

Driver

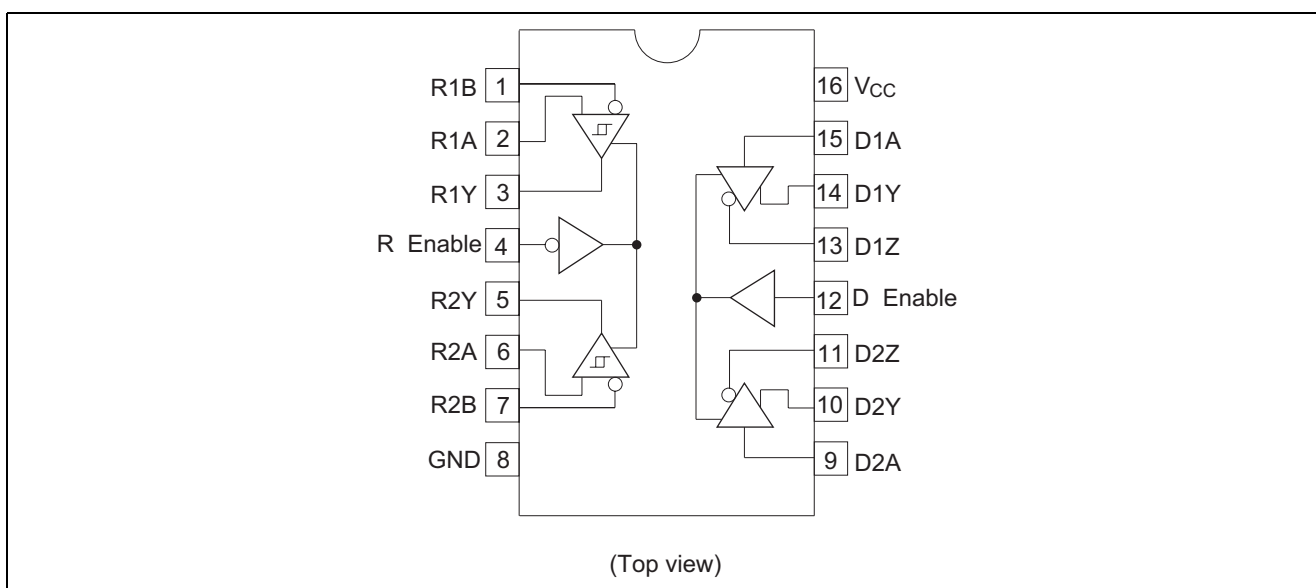
- Built in current restriction when short circuit
- Power up/down protection.
- High output current $I_{OH} = -40 \text{ mA}$
 $I_{OL} = 40 \text{ mA}$

Receiver

- Input hysteresis (Typ. 50 mV)
- In phase input voltage $\pm 200 \text{ mV}$ of input sensitivity in the range -7 to $+12 \text{ V}$.
- Ordering Information

Part Name	Package Type	Package Code	Package Abbreviation	Taping Abbreviation (Quantity)
HD29050P	DILP-16 pin	DP-16E, -16FV	P	—

Pin Arrangement



Function Table

Drivers				Receivers		
Input A	Enable	Output Y	Output Z	Differential Input A – B	Enable	Output Y
L	H	L	H	$V_{ID} \geq 0.2 \text{ V}$	L	H
H	H	H	L	$-0.2 \text{ V} < V_{ID} < 0.2 \text{ V}$	L	?
X	L	Z	Z	$V_{ID} \leq -0.2 \text{ V}$	H	Z
				X	H	Z

H : High level

L : Low level

Z : High impedance

X : Immaterial

? : Irrelevant

Absolute Maximum Ratings

Item	Symbol	Ratings	Unit
Supply Voltage*1	V_{CC}	7	V
Input Voltage A, B*3	V_{IN}	± 25	V
Differential Input Voltage*2*3	V_{ID}	± 25	V
Output Current*3	I_O	50	mA
Enable Input Voltage	V_{IE}	5.5	V
Input Voltage*4	V_{IN}	5.5	V
Output Applied Voltage*4*5	V_O	-1.0 to 7.0	V
Operating Temperature Range	T_{opr}	0 to 70	°C
Storage Temperature Range	T_{stg}	-65 to 150	°C

Notes: 1. All voltage values except for differential input voltage are with respect to network ground terminal.

2. Differential input voltage is measured at the noninverting input with respect to the corresponding inverting input.

3. Only receiver

4. Only driver

5. Z state

6. The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

Recommended Operating Conditions

Item	Symbol	Min	Typ	Max	Unit
Supply Voltage	V_{CC}	4.75	5.0	5.25	V
In Phase Input Voltage*1	V_{IC}	-7.0	—	12	V
Differential Input Voltage*1	V_{ID}	-6.0	—	6.0	V
Enable Input Voltage	V_{IE}	0	—	5.25	V
Input Voltage*2	V_{IN}	0	—	5.25	V
Operating Temperature	T_{opr}	0	25	70	°C

Notes: 1. Only receiver

2. Only driver

Electrical Characteristics (Ta = 0 to +70°C)

Driver

Item	Symbol	Min	Typ	Max	Unit	Conditions
Input Voltage	V_{IHD}	2.0	—	—	V	
	V_{ILD}	—	—	0.8	V	
Input Clamp Voltage	V_{IKD}	—	—	-1.5	V	$V_{CC} = 4.75\text{ V}$, $I_I = -18\text{ mA}$
Output Voltage	V_{OHD}	2.5	—	—	V	$V_{CC} = 4.75\text{ V}$, $I_{OH} = -20\text{ mA}$
		2.4	—	—	V	$V_{CC} = 4.75\text{ V}$, $I_{OH} = -40\text{ mA}$
	V_{OLD}	—	—	0.45	V	$V_{CC} = 4.75\text{ V}$, $I_{OL} = 20\text{ mA}$
		—	—	0.5	V	$V_{CC} = 4.75\text{ V}$, $I_{OL} = 40\text{ mA}$
Output Leak Current	I_{OZD}	-100	—	100	μA	$V_{CC} = 5.25\text{ V}$, $V_O = 0.5\text{ V}$, Enable = 0.8 V
		-100	—	100	μA	$V_{CC} = 5.25\text{ V}$, $V_O = 2.7\text{ V}$, Enable = 0.8 V
	$I_{O(Off)}$	—	—	-100	μA	$V_{CC} = 0\text{ V}$, $V_O = -0.25\text{ V}$
		—	—	-100	μA	$V_{CC} = 0\text{ V}$, $V_O = 6.0\text{ V}$
Input Current	I_{ID}	—	—	100	μA	$V_{CC} = 5.25\text{ V}$, $V_I = 5.25\text{ V}$
	I_{IHD}	—	—	20	μA	$V_{CC} = 5.25\text{ V}$, $V_I = 2.7\text{ V}$
	I_{ILD}	—	—	-360	μA	$V_{CC} = 5.25\text{ V}$, $V_I = 0.4\text{ V}$
Differential Output Voltage	$\Delta V_{OC} $	—	—	0.4	V	
	$ V_{OD2} $	2.0	—	—	V	
	$\Delta V_{OD} $	—	—	0.4	V	
Short Circuit Output Current*1	I_{OSD}	-30	—	-150	mA	$V_{CC} = 5.25\text{ V}$, $V_O = 0\text{ V}$

Electrical Characteristics (Ta = 0 to +70°C)

Receiver

Item	Symbol	Min	Typ	Max	Unit	Conditions
Differential Input Threshold Voltage*2	V _{THR}	—	—	0.2	V	V _O ≥ 2.7 V -7.0 V < V _{IC} < 12 V
		-0.2	—	—	V	V _O ≤ 0.45 V -7.0 V < V _{IC} < 12 V
Input Current	I _{IBR}	—	—	1.0	mA	V _{IN} ≤ V _{I2} , 0 V, V _{CC} ≤ 5.25 V
		—	—	-0.8	mA	V _{IN} ≤ V _{I7} , 0 V, V _{CC} ≤ 5.25 V
Output Voltage	V _{OHR}	2.7	—	—	V	V _{CC} = 4.75 V, I _O = -400 mA V _{ID} = 0.4 V, -7.0 V < V _{ICM} < 12 V
	V _{OLR}	—	—	0.45	V	V _{CC} = 4.75 V, I _O = 8.0 mA V _{ID} = -0.4 V, -7.0 V < V _{ICM} < 12 V
Output Leak Current	I _{OZR}	-100	—	100	mA	V _{CC} = 5.25 V, V _O = 0.4 V V _{ID} = 3.0 V, Enable = 2.0 V
		-100	—	100	mA	V _{CC} = 5.25 V, V _O = 2.4 V V _{ID} = -3.0 V, Enable = 2.0 V
Short Circuit Output Current*1	I _{OSR}	-15	—	-85	mA	V _{CC} = 5.25 V, V _O = 0 V V _{ID} = 3.0 V
Input Voltage	V _{IHE}	2.0	—	—	V	
	V _{ILE}	—	—	0.8	V	
Input Current	I _{IIE}	—	—	-100	μA	V _{CC} = 5.25 V, V _{IL} = 0.4 V
	I _{IHE}	—	—	20	μA	V _{CC} = 5.25 V, V _{IH} = 2.7 V
	I _{IE}	—	—	100	μA	V _{CC} = 5.25 V, V _{IH} = 5.25 V
Input Clamp Voltage	V _{IKE}	—	—	-1.5	V	V _{CC} = 4.75, I _I = -18 mA

Supply

Item	Symbol	Min	Typ	Max	Unit	Conditions
Supply Current	I _{CC}	—	55*3	80	mA	V _{CC} = 5.25 V

- Notes: 1. Not more than one output should be shorted at a time, and duration of the short circuit should not exceed one second.
 2. In this table, only the threshold voltage is expressed in algebra.
 3. All typical values are at V_{CC} = 5 V, Ta = 25°C.

Switching Characteristics ($T_a = 25^\circ\text{C}$, $V_{CC} = 5\text{ V}$)**Driver**

Item	Symbol	Min	Typ	Max	Unit	Conditions
Propagation Delay Time	t_{PLHD}	—	—	20	ns	$C_L = 30\text{ pF}$, $R_L = 75\ \Omega$ to GND $R_L = 180\ \Omega$ to V_{CC}
	t_{PHLD}	—	—	20	ns	$C_L = 30\text{ pF}$, $R_L = 75\ \Omega$ to GND $R_L = 180\ \Omega$ to V_{CC}
Propagation Delay Time Difference	t_{SKD}^{*1}	—	—	4	ns	$C_L = 30\text{ pF}$, $R_L = 75\ \Omega$ to GND $R_L = 180\ \Omega$ to V_{CC}
Output Enable Time	t_{ZHD}	—	—	20	ns	$C_L = 30\text{ pF}$, $R_L = 75\ \Omega$ to GND
	t_{ZLD}	—	—	35	ns	$C_L = 30\text{ pF}$, $R_L = 180\ \Omega$ to V_{CC}
Output Disable Time	t_{HZD}	—	—	20	ns	$C_L = 10\text{ pF}$, $R_L = 75\ \Omega$ to GND
	t_{LZD}	—	—	25	ns	$C_L = 10\text{ pF}$

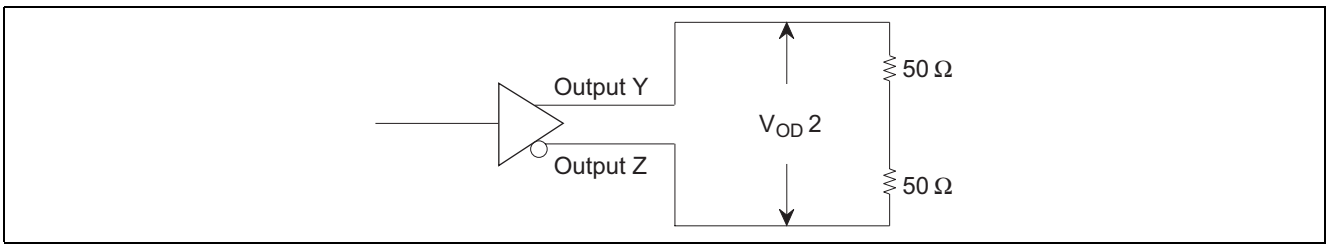
Receiver

Item	Symbol	Min	Typ	Max	Unit	Conditions
Propagation Delay Time	t_{PLHR}	—	—	40	ns	$C_L = 15\text{ pF}$
	t_{PHLR}	—	—	40	ns	$C_L = 15\text{ pF}$
Output Enable Time	t_{ZHR}	—	—	20	ns	$C_L = 15\text{ pF}$, $R_L = 5\text{ K}\Omega$ to GND
	t_{ZLR}	—	—	25	ns	$C_L = 15\text{ pF}$, $R_L = 2\text{ K}\Omega$ to V_{CC}
Output Disable Time	t_{HZR}	—	—	30	ns	$C_L = 15\text{ pF}$, $R_L = 5\text{ K}\Omega$ to GND $R_L = 2\text{ K}\Omega$ to V_{CC}
	t_{LZR}	—	—	30	ns	

Note: 1. $t_{SKD} = |t_{PLHD} - t_{PHLD}|$

DC Test ($|V_{OD2}|$, $\Delta |V_{OD}|$, V_{OC} , $\Delta |V_{OC}|$)

$|V_{OD2}|$, $\Delta |V_{OD}|$ Test



V_{OC} , $\Delta |V_{OC}|$ Test

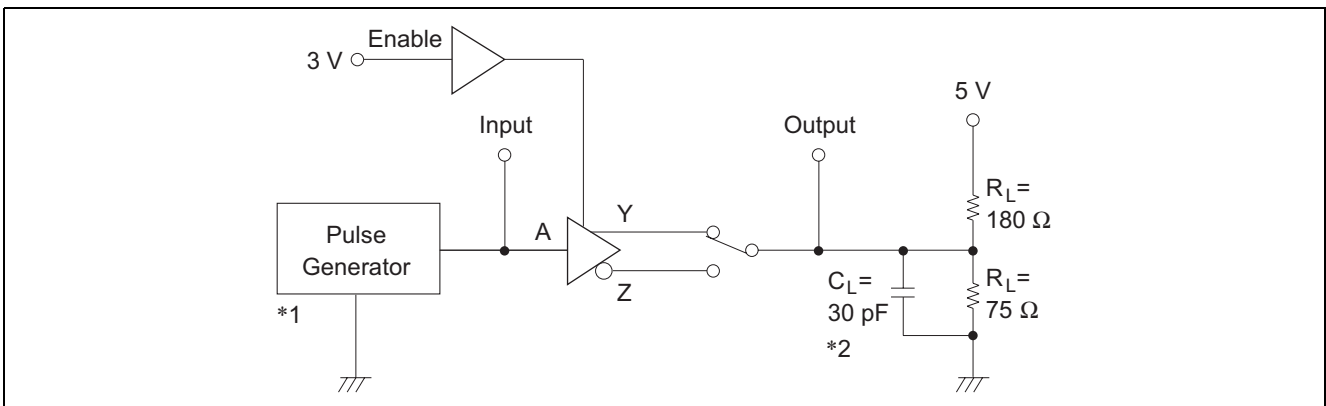
Note: $|V_{OD}|$ and $\Delta |V_{OC}|$ indicate the differences of voltage from the former states when Y and Z outputs are inverted.

$$\Delta |V_{OD}| = ||V_{OD2}| - |V_{OD2}||$$

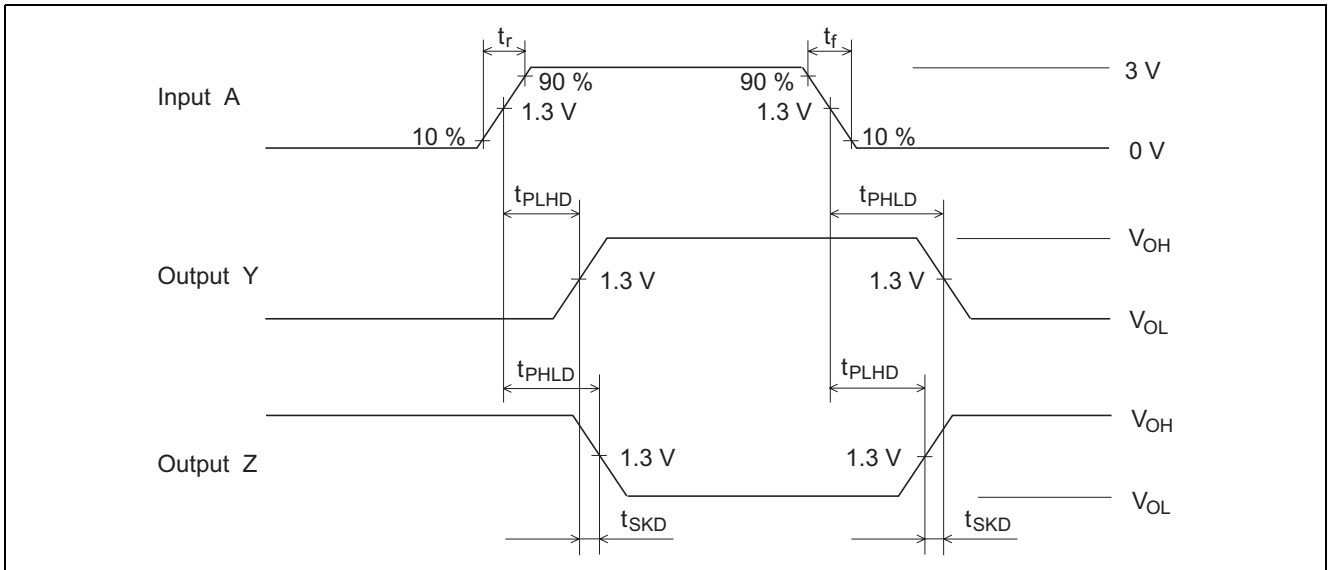
$$\Delta |V_{OC}| = |V_{OC} - V_{OC}|$$

1. t_{PLHD} , t_{PHLD}

Test circuit

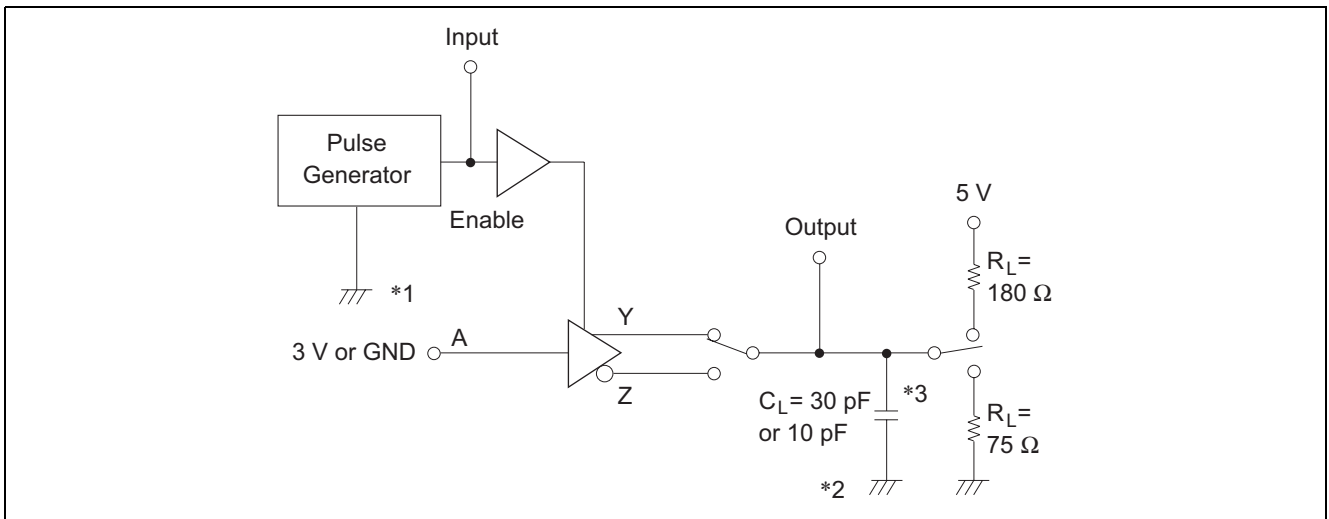


Waveforms

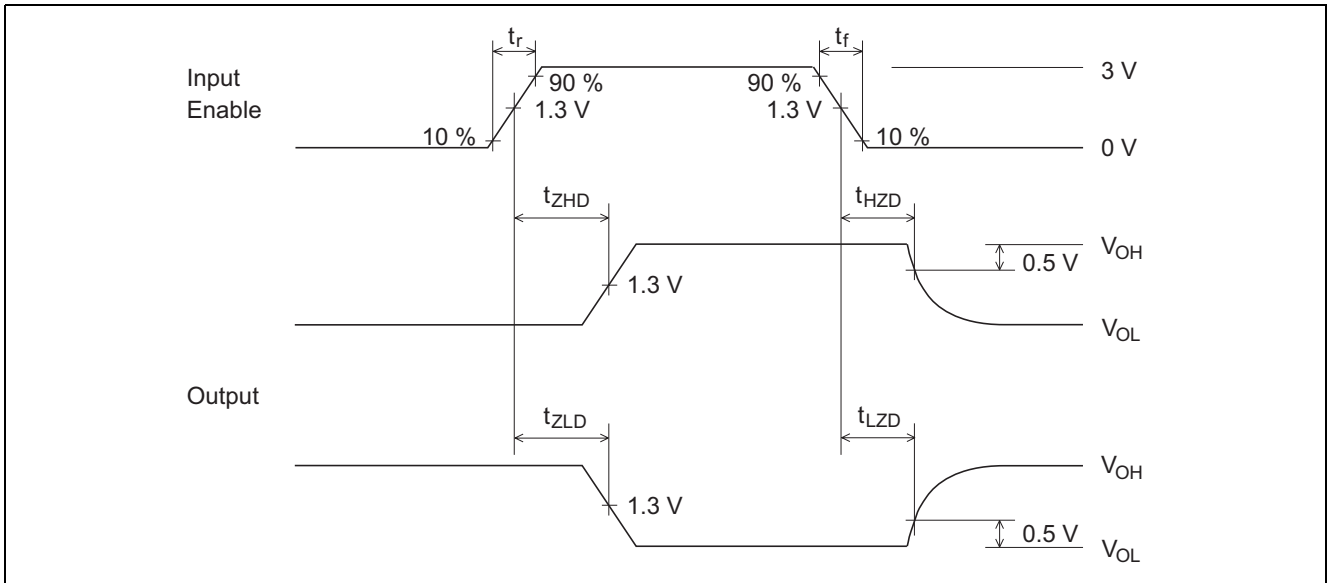


2. t_{zHD} , t_{zLD} , t_{HzD} , t_{LzD}

Test circuit

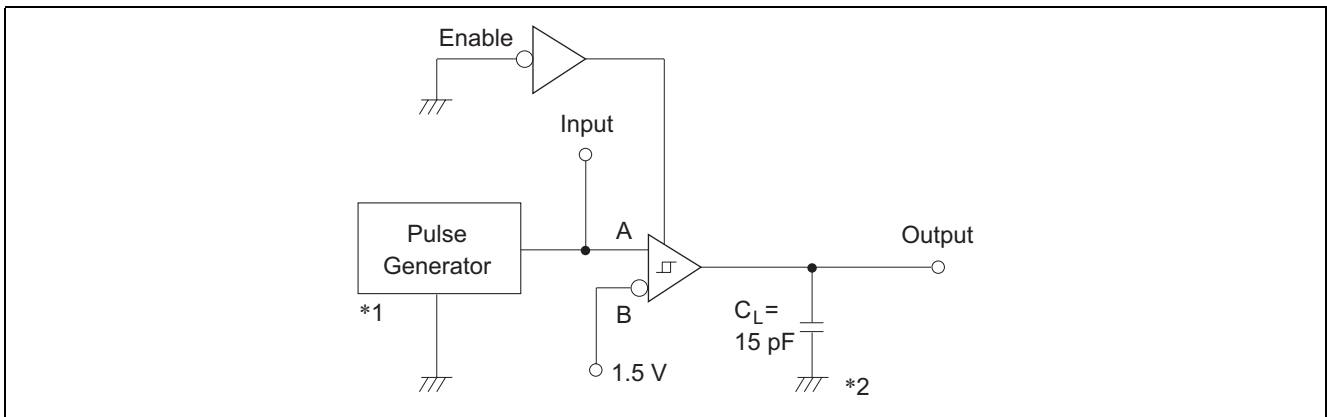


Waveforms

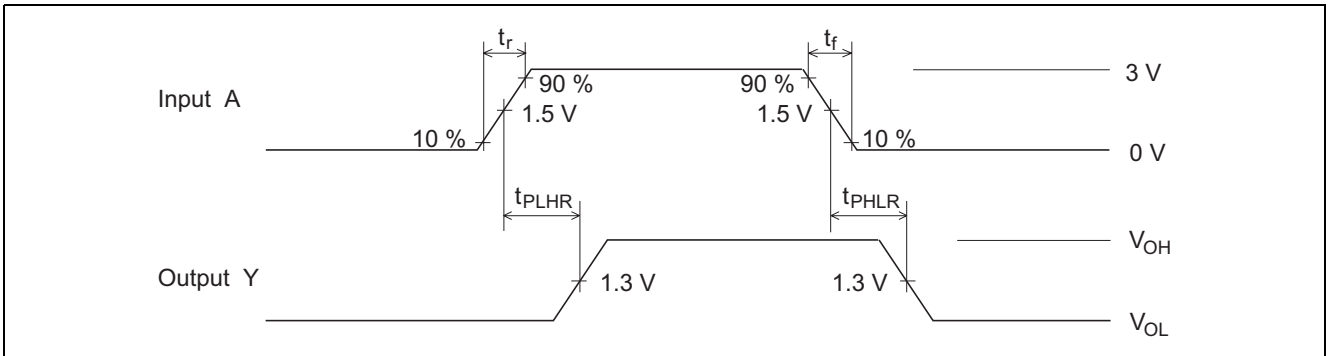


3. t_{PLHR} , t_{PHLR}

Test circuit

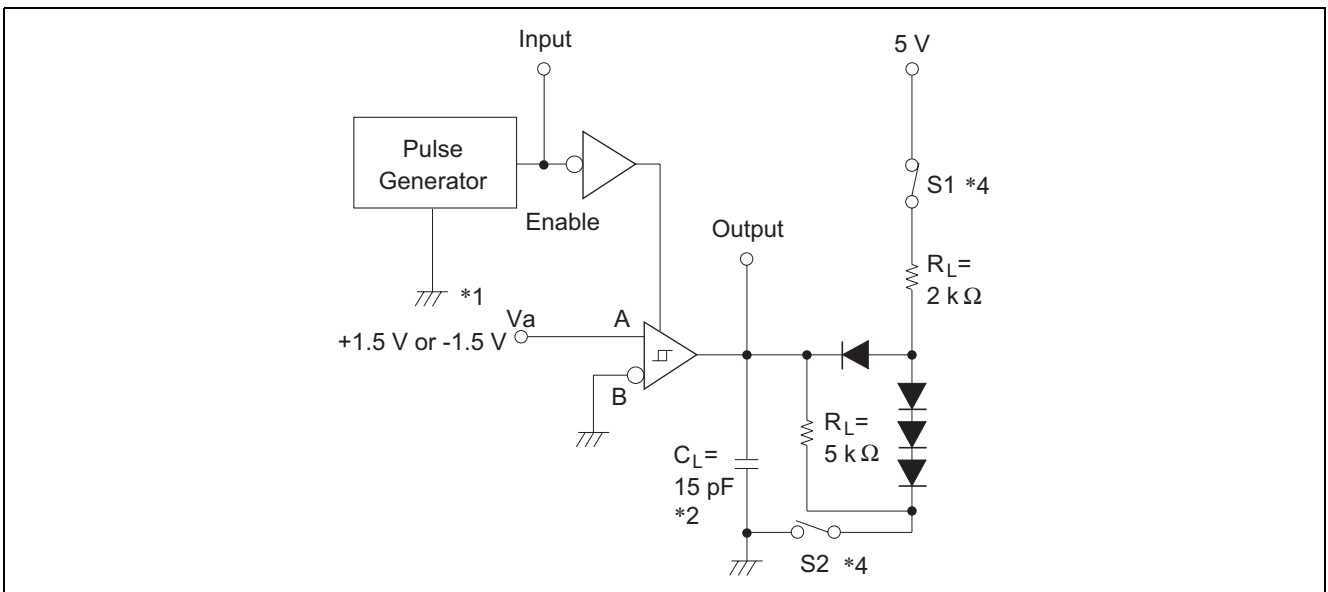


Waveforms

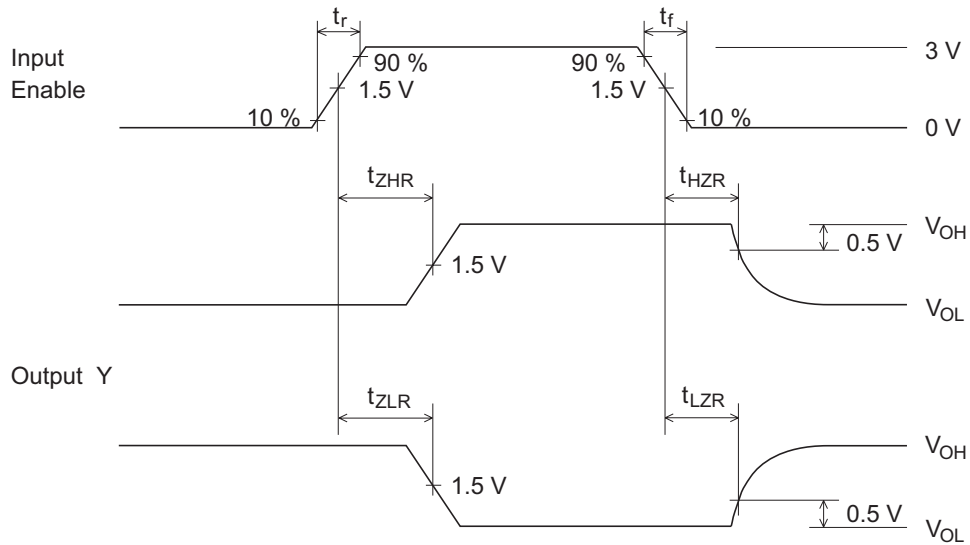


4. t_{ZHR} , t_{ZLR} , t_{HZR} , t_{LZR}

Test circuit

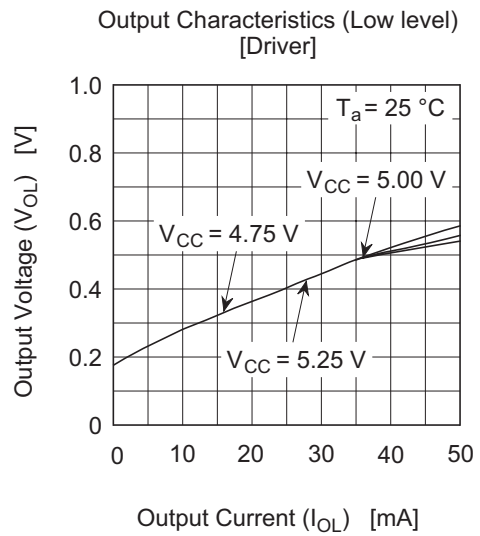
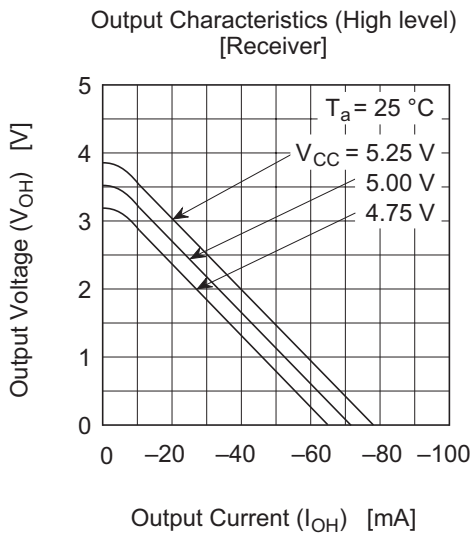
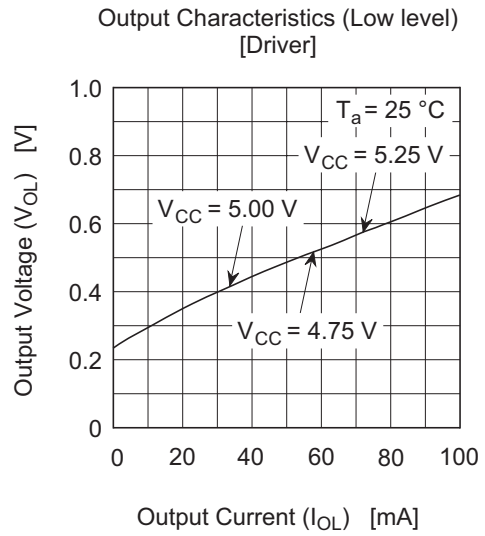
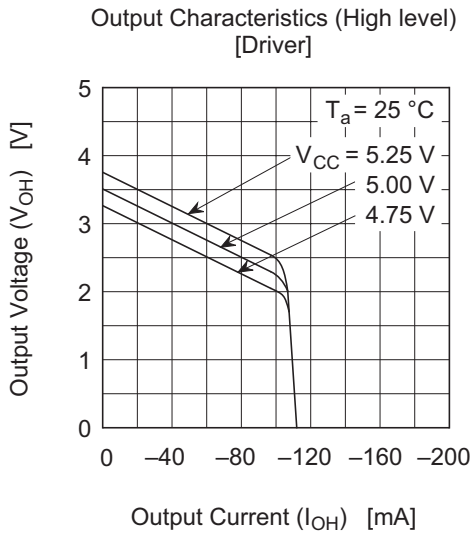


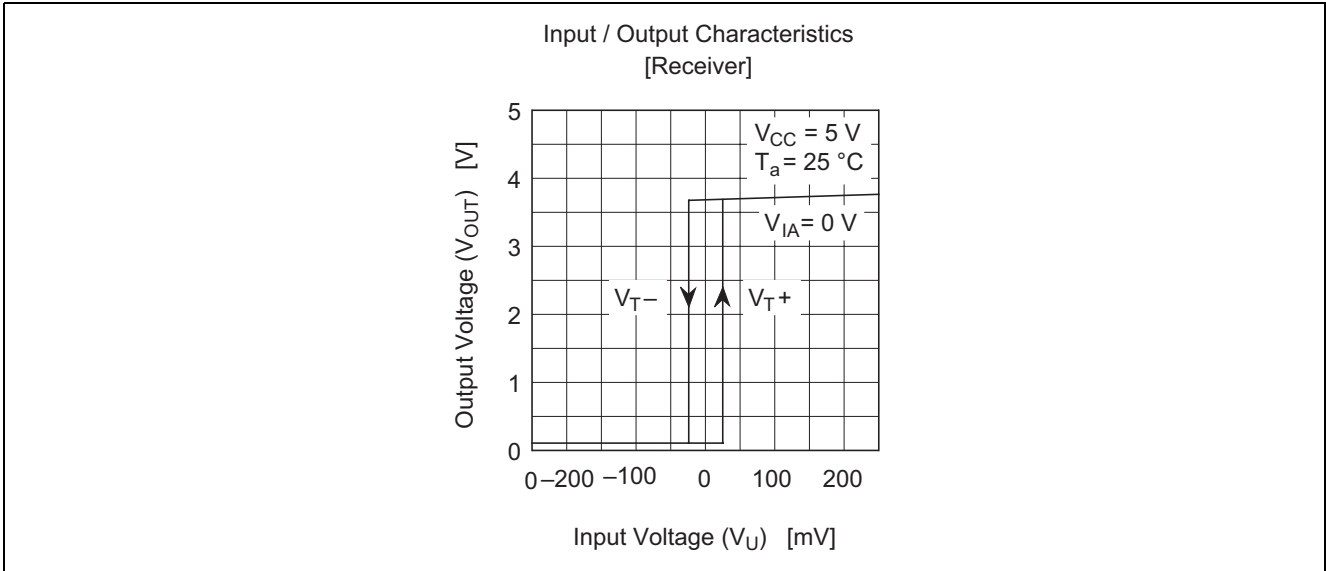
Waveforms



- Notes:
1. The pulse generator has the following characteristics:
 PRR = 1 MHz, 50% duty cycle, $t_r = t_f = 6.0$ ns.
 2. C_L includes probe and jig capacitance.
 3. 75 Ω connected between the pin and GND at t_{ZHD} t_{HZD} test.
 180 Ω connected between the pin and GND at t_{ZHD} t_{HZD} test.
 4. At t_{HZR} , t_{LZR} test, S_1 and S_2 are closed.
 At t_{ZHR} test, S_1 is open and S_2 is closed.
 At t_{ZLR} test, S_1 is closed and S_2 is open.

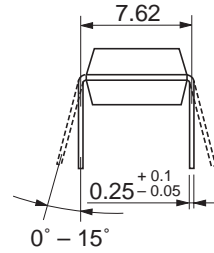
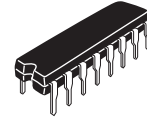
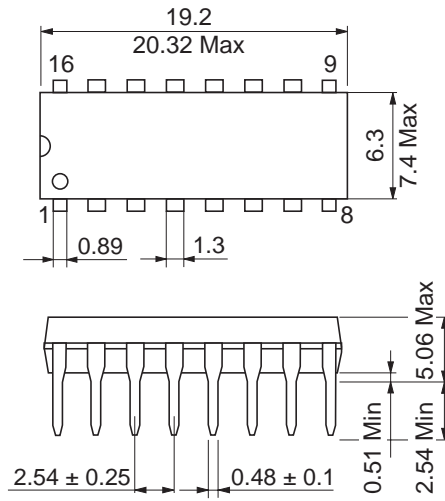
Main Characteristics





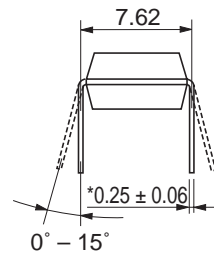
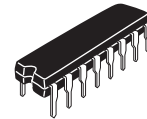
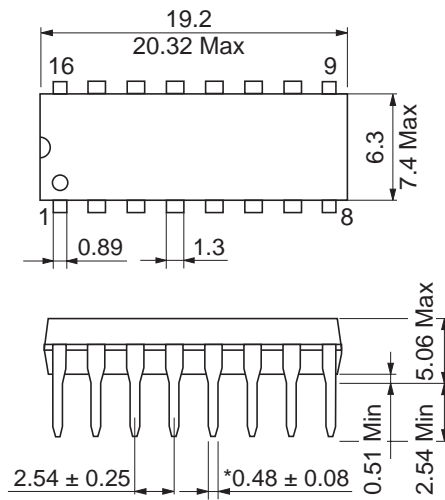
Package Dimensions

As of January, 2003
Unit: mm



Package Code	DP-16E
JEDEC	Conforms
JEITA	Conforms
Mass (reference value)	1.05 g

Unit: mm



*Ni/Pd/AU Plating

Package Code	DP-16FV
JEDEC	Conforms
JEITA	Conforms
Mass (reference value)	1.05 g

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